

CD4020BMS, CD4024BMS, CD4040BMS

CMOS Ripple-Carry BinaryCounter/Dividers

FN3300 Rev 1.00 October 1996

Features

- · High Voltage Types (20V Rating)
- Medium Speed Operation
- · Fully Static Operation
- · Buffered Inputs and Outputs
- 100% Tested for Quiescent Current at 20V
- Standardized Symmetrical Output Characteristics
- Common Reset
- 5V, 10V and 15V Parametric Ratings
- Maximum Input Current of 1μa at 18V Over Full Package-Temperature Range;
 - 100nA at 18V and 25°C
- Noise Margin (Over Full Package Temperature Range):
 - 1V at VDD = 5V
 - 2V at VDD = 10V
 - 2.5V at VDD = 15V
- Meets All Requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications For Description Of 'B' Series CMOS Devices"

Applications

- Control Counters
- Timers
- Frequency Dividers
- · Time-Delay Circuits

Description

CD4020BMS - 14 Stage CD4024BMS - 7 Stage CD4040BMS - 12 Stage

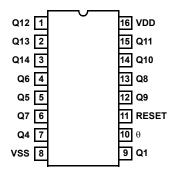
CD4020BMS, CD4024BMS, and CD4040BMS are ripple-carry binary counters. All counter stages are master-slave flip-flops. The state of a counter advances one count on the negative transition of each input pulse; a high level on the RESET line resets the counter to its all zeros state. Schmitt trigger action on the input-pulse line permits unlimited rise and fall times. All inputs and outputs are buffered.

The CD4020BMS, CD4024BMS and the CD4040BMS is supplied in these 14 lead outline packages:

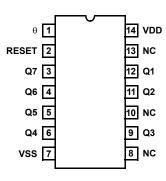
| | CD4020B | CD4024B | CD4040B |
|------------------|---------|---------|---------|
| Braze Seal DIP | H4W | H4Q | H4X |
| Frit Seal DIP | H1F | H1B | H1F |
| Ceramic Flatpack | H6W | H3W | H6W |

Pinouts

CD4020BMS TOP VIEW

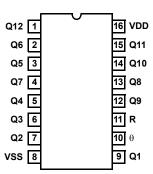


CD4024BMS TOP VIEW



NC = NO CONNECTION

CD4040BMS TOP VIEW



Absolute Maximum Ratings

DC Supply Voltage Range, (VDD) ... -0.5V to +20V (Voltage Referenced to VSS Terminals) Input Voltage Range, All Inputs ... -0.5V to VDD +0.5V DC Input Current, Any One Input ... ± 10 mA Operating Temperature Range ... -55°C to +125°C Package Types D, F, K, H Storage Temperature Range (TSTG) ... -65°C to +150°C Lead Temperature (During Soldering) ... ± 265 °C At Distance 1/16 \pm 1/32 Inch (1.59mm \pm 0.79mm) from case for 10s Maximum

Reliability Information

| Thermal Resistance | θ_{ja} | $\theta_{\sf ic}$ |
|--|---------------|-------------------|
| Ceramic DIP and FRIT Package | 80°Č/W | 20°C/W |
| Flatpack Package | 70°C/W | 20°C/W |
| Maximum Package Power Dissipation (PD | O) at +125°C | 0 |
| For TA = -55°C to +100°C (Package Ty | pe D, F, K) | 500mW |
| For TA = $+100^{\circ}$ C to $+125^{\circ}$ C (Package 7 | Type D, F, k | () Derate |
| Lin | earity at 12 | mW/°C to 200mW |
| Device Dissipation per Output Transistor. | | 100mW |
| For TA = Full Package Temperature Ra | inge (All Pa | ckage Types) |
| Junction Temperature | | +175°C |

TABLE 1. DC ELECTRICAL PERFORMANCE CHARACTERISTICS

| | | | | GROUP A | | LIN | IITS | |
|--------------------------------|--------|-----------------------------------|-----------------------|-----------|----------------------|-------------|-------|-------|
| PARAMETER | SYMBOL | CONDITIONS (| NOTE 1) | SUBGROUPS | TEMPERATURE | MIN | MAX | UNITS |
| Supply Current | IDD | VDD = 20V, VIN = VD | D or GND | 1 | +25°C | - | 10 | μΑ |
| | | | | 2 | +125°C | - | 1000 | μА |
| | | VDD = 18V, VIN = VD | D or GND | 3 | -55°C | - | 10 | μА |
| Input Leakage Current | IIL | VIN = VDD or GND | VDD = 20 | 1 | +25°C | -100 | - | nA |
| | | | | 2 | +125°C | -1000 | - | nA |
| | | | VDD = 18V | 3 | -55°C | -100 | - | nA |
| Input Leakage Current | IIH | VIN = VDD or GND | VDD = 20 | 1 | +25°C | - | 100 | nA |
| | | | | 2 | +125°C | - | 1000 | nA |
| | | | VDD = 18V | 3 | -55°C | - | 100 | nA |
| Output Voltage | VOL15 | VDD = 15V, No Load | • | 1, 2, 3 | +25°C, +125°C, -55°C | - | 50 | mV |
| Output Voltage | VOH15 | VDD = 15V, No Load (| Note 3) | 1, 2, 3 | +25°C, +125°C, -55°C | 14.95 | - | V |
| Output Current (Sink) | IOL5 | VDD = 5V, VOUT = 0.4 | VDD = 5V, VOUT = 0.4V | | +25°C | 0.53 | - | mA |
| Output Current (Sink) | IOL10 | VDD = 10V, VOUT = 0.5V | | 1 | +25°C | 1.4 | - | mA |
| Output Current (Sink) | IOL15 | VDD = 15V, VOUT = 1.5V | | 1 | +25°C | 3.5 | - | mA |
| Output Current (Source) | IOH5A | VDD = 5V, VOUT = 4.0 | VDD = 5V, VOUT = 4.6V | | +25°C | - | -0.53 | mA |
| Output Current (Source) | IOH5B | VDD = 5V, VOUT = 2.5 | 5V | 1 | +25°C | - | -1.8 | mA |
| Output Current (Source) | IOH10 | VDD = 10V, VOUT = 9 |).5V | 1 | +25°C | - | -1.4 | mA |
| Output Current (Source) | IOH15 | VDD = 15V, VOUT = 1 | 3.5V | 1 | +25°C | - | -3.5 | mA |
| N Threshold Voltage | VNTH | VDD = 10V, ISS = -10 | μΑ | 1 | +25°C | -2.8 | -0.7 | V |
| P Threshold Voltage | VPTH | VSS = 0V, IDD = 10μΑ | ١ | 1 | +25°C | 0.7 | 2.8 | V |
| Functional | F | VDD = 2.8V, VIN = VD | D or GND | 7 | +25°C | VOH > | VOL < | V |
| | | VDD = 20V, VIN = VD | D or GND | 7 | +25°C | VDD/2 VDD/2 | | |
| | | VDD = 18V, VIN = VD | D or GND | 8A | +125°C | | | |
| | | VDD = 3V, VIN = VDD | or GND | 8B | -55°C | | | |
| Input Voltage Low (Note 2) | VIL | VDD = 5V, VOH > 4.5 | V, VOL < 0.5V | 1, 2, 3 | +25°C, +125°C, -55°C | - | 1.5 | V |
| Input Voltage High (Note 2) | VIH | VDD = 5V, VOH > 4.5 | V, VOL < 0.5V | 1, 2, 3 | +25°C, +125°C, -55°C | 3.5 | - | V |
| Input Voltage Low (Note 2) | VIL | VDD = 15V, VOH > 13 VOL < 1.5V | 5.5V, | 1, 2, 3 | +25°C, +125°C, -55°C | - | 4 | V |
| Input Voltage High (Note 2) | VIH | VDD = 15V, VOH > 13 VOL < 1.5V | 5.5V, | 1, 2, 3 | +25°C, +125°C, -55°C | 11 | - | V |

TABLE 1. DC ELECTRICAL PERFORMANCE CHARACTERISTICS

| | | | GROUP A | | LIM | IITS | | |
|-----------|--------|---------------------|-----------|-------------|-----|------|-------|--|
| PARAMETER | SYMBOL | CONDITIONS (NOTE 1) | SUBGROUPS | TEMPERATURE | MIN | MAX | UNITS | |

plemented.

2. Go/No Go test with limits applied to inputs

NOTES: 1. All voltages referenced to device GND, 100% testing being im- 3. For accuracy, voltage is measured differentially to VDD. Limit is 0.050V max.

TABLE 2. AC ELECTRICAL PERFORMANCE CHARACTERISTICS

| | | | GROUP A | | LIM | STII | |
|-----------------------------------|----------------|----------------------------|-----------|---------------|------|------|-------|
| PARAMETER | SYMBOL | CONDITIONS (NOTE 1, 2) | SUBGROUPS | TEMPERATURE | MIN | MAX | UNITS |
| Propagation Delay | TPHL1 | VDD = 5V, VIN = VDD or GND | 9 | +25°C | - | 360 | ns |
| 0 To Q1 | TPLH1 | | 10, 11 | +125°C, -55°C | - | 486 | ns |
| Propagation Delay Qn To Qn + 1 | TPHL2 | VDD = 5V, VIN = VDD or GND | 9 | +25°C | - | 330 | ns |
| | TPLH2 | | 10, 11 | +125°C, -55°C | - | 446 | ns |
| Propagation Delay | TPLH3 TPHL3 | VDD = 5V, VIN = VDD or GND | 9 | +25°C | - | 280 | ns |
| Reset To Q | | | 10, 11 | +125°C, -55°C | - | 378 | ns |
| Transition Time | TTHL | VDD = 5V, VIN = VDD or GND | 9 | +25°C | - | 200 | ns |
| Q1 | TTLH | | 10, 11 | +125°C, -55°C | - | 270 | ns |
| Maximum Clock Input Fre- | FCL | VDD = 5V, VIN = VDD or GND | 9 | +25°C | 3.5 | - | MHz |
| quency | | | 10, 11 | +125°C, -55°C | 2.22 | - | MHz |

NOTES:

- 1. VDD = 5V, CL = 50pF, RL = 200K
- 2. -55° C and $+125^{\circ}$ C limits guaranteed, 100% testing being implemented.

TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS

| | | | | | LIMITS | | |
|-----------------------|--------|-----------------------------|-------|--------------------------|--------|-----|-------|
| PARAMETER | SYMBOL | CONDITIONS | NOTES | TEMPERATURE | MIN | MAX | UNITS |
| Supply Current | IDD | VDD = 5V, VIN = VDD or GND | 1, 2 | -55°C, +25°C | - | 5 | μΑ |
| | | | | +125°C | 1 | 150 | μΑ |
| | | VDD = 10V, VIN = VDD or GND | 1, 2 | -55°C, +25°C | - | 10 | μА |
| | | | | +125°C | - | 300 | μΑ |
| | | VDD = 15V, VIN = VDD or GND | 1, 2 | -55°C, +25°C | - | 10 | μΑ |
| | | | | +125°C | - | 600 | μΑ |
| Output Voltage | VOL | VDD = 5V, No Load | 1, 2 | +25°C, +125°C, - 55°C | - | 50 | mV |
| Output Voltage | VOL | VDD = 10V, No Load | 1, 2 | +25°C, +125°C, - 55°C | - | 50 | mV |
| Output Voltage | VOH | VDD = 5V, No Load | 1, 2 | +25°C, +125°C, - 55°C | 4.95 | - | V |
| Output Voltage | VOH | VDD = 10V, No Load | 1, 2 | +25°C, +125°C, - 55°C | 9.95 | - | V |
| Output Current (Sink) | IOL5 | VDD = 5V, VOUT = 0.4V | 1, 2 | +125°C | 0.36 | - | mA |
| | | | | -55°C | 0.64 | - | mA |
| Output Current (Sink) | IOL10 | VDD = 10V, VOUT = 0.5V | 1, 2 | +125°C | 0.9 | - | mA |
| | | | | -55°C | 1.6 | - | mA |
| Output Current (Sink) | IOL15 | VDD = 15V, VOUT = 1.5V | 1, 2 | +125°C | 2.4 | - | mA |
| | | | | -55°C | 4.2 | - | mA |

TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS (Continued)

| | | | | | LIN | IITS | |
|--------------------------|-----------------|-------------------------------|---------|--------------------------|-----|-------|-------|
| PARAMETER | SYMBOL | CONDITIONS | NOTES | TEMPERATURE | MIN | MAX | UNITS |
| Output Current (Source) | IOH5A | VDD = 5V, VOUT = 4.6V | 1, 2 | +125°C | - | -0.36 | mA |
| | | | | -55°C | - | -0.64 | mA |
| Output Current (Source) | IOH5B | VDD = 5V, VOUT = 2.5V | 1, 2 | +125°C | - | -1.15 | mA |
| | | -55°C - | | -2.0 | mA | | |
| Output Current (Source) | IOH10 | VDD = 10V, VOUT = 9.5V | 1, 2 | +125°C | = | -0.9 | mA |
| | | | | -55°C | = | -1.6 | mA |
| Output Current (Source) | IOH15 | VDD =15V, VOUT = 13.5V | 1, 2 | +125°C | = | -2.4 | mA |
| | | | | -55°C | - | -4.2 | mA |
| Input Voltage Low | VIL | VDD = 10V, VOH > 9V, VOL < 1V | 1, 2 | +25°C, +125°C, - 55°C | - | 3 | V |
| Input Voltage High | VIH | VDD = 10V, VOH > 9V, VOL < 1V | 1, 2 | +25°C, +125°C, - 55°C | 7 | - | V |
| Propagation Delay | TPHL1 VDD = 10V | | 1, 2, 3 | +25°C | - | 160 | ns |
| Input To Q1 | TPLH1 | VDD = 15V | 1, 2, 3 | +25°C | - | 130 | ns |
| Propagation Delay TPHL | | VDD = 10V | 1, 2, 3 | +25°C | - | 80 | ns |
| QN To QN + 1 | TPLH2 | VDD = 15V | 1, 2, 3 | +25°C | = | 60 | ns |
| Propagation Delay | TPHL3 | VDD = 10V | 1, 2, 3 | +25°C | = | 120 | ns |
| Reset To Q | | VDD = 15V | 1, 2, 3 | +25°C | = | 100 | ns |
| Transition Time | TTHL | VDD = 10V | 2, 3 | +25°C | = | 100 | ns |
| | TTLH | VDD = 15V | 2, 3 | +25°C | - | 80 | ns |
| Maximum Clock Input Fre- | FCL | VDD = 10V | 1, 2, 3 | +25°C | 8 | - | MHz |
| quency | | VDD = 15V | 1, 2, 3 | +25°C | 12 | - | MHz |
| Minimum Reset Pulse | TW | VDD = 5V | 1, 2, 3 | +25°C | = | 200 | ns |
| Width | | VDD = 10V | 1, 2, 3 | +25°C | = | 80 | ns |
| | | VDD = 15V | 1, 2, 3 | +25°C | = | 60 | ns |
| Reset Removal Time | TREM | VDD = 5V | 1, 2, 3 | +25°C | - | 350 | ns |
| | | VDD = 10V | 1, 2, 3 | +25°C | - | 150 | ns |
| | | VDD = 15V | 1, 2, 3 | +25°C | - | 100 | ns |
| Minimum Input Pulse | TW | VDD = 5V | 1, 2, 3 | +25°C | - | 140 | ns |
| Width | | VDD = 10V | 1, 2, 3 | +25°C | - | 60 | ns |
| | | VDD = 15V | 1, 2, 3 | +25°C | - | 40 | ns |
| Input Capacitance | CIN | Any Input | 1, 2 | +25°C | - | 7.5 | pF |

NOTES:

- 1. All voltages referenced to device GND.
- 2. The parameters listed on Table 3 are controlled via design or process and are not directly tested. These parameters are characterized on initial design release and upon design changes which would affect these characteristics.
- 3. CL = 50pF, RL = 200K, Input TR, TF < 20ns.

TABLE 4. POST IRRADIATION ELECTRICAL PERFORMANCE CHARACTERISTICS

| | | | | | LIMITS | | |
|---------------------|--------|-----------------------------|-------|-------------|--------|------|-------|
| PARAMETER | SYMBOL | CONDITIONS | NOTES | TEMPERATURE | MIN | MAX | UNITS |
| Supply Current | IDD | VDD = 20V, VIN = VDD or GND | 1, 4 | +25°C | - | 25 | μА |
| N Threshold Voltage | VNTH | VDD = 10V, ISS = -10μ A | 1, 4 | +25°C | -2.8 | -0.2 | V |



TABLE 4. POST IRRADIATION ELECTRICAL PERFORMANCE CHARACTERISTICS (Continued)

| | | | | | LIMITS | | |
|------------------------------|--------------|-----------------------------|------------|-------------|--------|--------------------------|-------|
| PARAMETER | SYMBOL | CONDITIONS | NOTES | TEMPERATURE | MIN | MAX | UNITS |
| N Threshold Voltage Delta | ΔVTND | VDD = 10V, ISS = -10μA | 1, 4 | +25°C | - | ±1 | V |
| P Threshold Voltage | VTP | VSS = 0V, IDD = 10μA | 1, 4 | +25°C | 0.2 | 2.8 | V |
| P Threshold Voltage Delta | ΔVTPD | VSS = 0V, IDD = 10μA | 1, 4 | +25°C | - | ±1 | V |
| Functional | F | VDD = 18V, VIN = VDD or GND | 1 | +25°C | VOH > | VOL < | V |
| | | VDD = 3V, VIN = VDD or GND | 1 | | VDD/2 | VDD/2 | |
| Propagation Delay Time | TPHL TPLH | VDD = 5V | 1, 2, 3, 4 | +25°C | - | 1.35 x +25°C Limit | ns |

NOTES: 1. All voltages referenced to device GND.

3. See Table 2 for +25°C limit.

2. CL = 50pF, RL = 200K, Input TR, TF < 20ns.

4. Read and Record

TABLE 5. BURN-IN AND LIFE TEST DELTA PARAMETERS $+25^{\rm O}{\rm C}$

| PARAMETER | SYMBOL | DELTA LIMIT |
|-------------------------|--------|--------------------------|
| Supply Current - MSI-2 | IDD | ± 1.0μA |
| Output Current (Sink) | IOL5 | ± 20% x Pre-Test Reading |
| Output Current (Source) | IOH5A | ± 20% x Pre-Test Reading |

TABLE 6. APPLICABLE SUBGROUPS

| CONFORMANCE GROUP | | MIL-STD-883 METHOD | GROUP A SUBGROUPS | READ AND RECORD |
|-------------------------------|------------------|-----------------------|---------------------------------------|------------------------------|
| Initial Test (P | re Burn-In) | 100% 5004 | 1, 7, 9 | IDD, IOL5, IOH5A |
| Interim Test | 1 (Post Burn-In) | 100% 5004 | 1, 7, 9 | IDD, IOL5, IOH5A |
| Interim Test 2 | 2 (Post Burn-In) | 100% 5004 | 1, 7, 9 | IDD, IOL5, IOH5A |
| PDA (Note 1) | | 100% 5004 | 1, 7, 9, Deltas | |
| Interim Test 3 (Post Burn-In) | | 100% 5004 | 1, 7, 9 | IDD, IOL5, IOH5A |
| PDA (Note | 1) | 100% 5004 | 1, 7, 9, Deltas | |
| Final Test | | 100% 5004 | 2, 3, 8A, 8B, 10, 11 | |
| Group A | | Sample 5005 | 1, 2, 3, 7, 8A, 8B, 9, 10, 11 | |
| Group B | Subgroup B-5 | Sample 5005 | 1, 2, 3, 7, 8A, 8B, 9, 10, 11, Deltas | Subgroups 1, 2, 3, 9, 10, 11 |
| | Subgroup B-6 | Sample 5005 | 1, 7, 9 | |
| Group D | • | Sample 5005 | 1, 2, 3, 8A, 8B, 9 | Subgroups 1, 2 3 |

NOTE: 1. 5% Parameteric, 3% Functional; Cumulative for Static 1 and 2.

TABLE 7. TOTAL DOSE IRRADIATION

| | MIL-STD-883 | TE | ST | READ AND | RECORD |
|--------------------|-------------|----------------------|---------|-----------|------------|
| CONFORMANCE GROUPS | METHOD | PRE-IRRAD POST-IRRAD | | PRE-IRRAD | POST-IRRAD |
| Group E Subgroup 2 | 5005 | 1, 7, 9 | Table 4 | 1, 9 | Table 4 |

TABLE 8. BURN-IN AND IRRADIATION TEST CONNECTIONS

| | | | | | OSCILLATOR | |
|-------------|-----------|--------|-----|----------------|------------|-------|
| FUNCTION | OPEN | GROUND | VDD | 9V \pm -0.5V | 50kHz | 25kHz |
| PART NUMBER | CD4020BMS | | | | | |



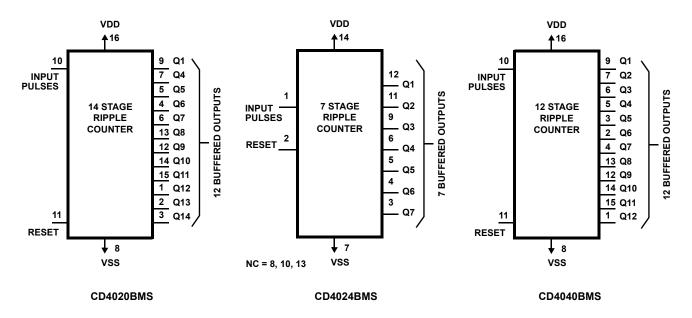
TABLE 8. BURN-IN AND IRRADIATION TEST CONNECTIONS (Continued)

| FUNCTION | OPEN | GROUND | VDD | 9V ± -0.5V | OSCILLATOR | |
|----------------------------|-------------------|-----------|------------|-------------------|------------|-------|
| | | | | | 50kHz | 25kHz |
| Static Burn-In 1 Note 1 | 1 - 7, 9, 12 - 15 | 8, 10, 11 | 16 | | | |
| Static Burn-In 2 Note 1 | 1 - 7, 9, 12 - 15 | 8 | 10, 11, 16 | | | |
| Dynamic Burn- In Note 1 | - | 8, 11 | 16 | 1 - 7, 9, 12 - 15 | 10 | |
| Irradiation Note 2 | 1 - 7, 9, 12 - 15 | 8 | 10, 11, 16 | | | |
| PART NUMBER | CD4024BMS | | • | • | | • |
| Static Burn-In 1 Note 1 | 3 - 6, 8 - 13 | 1, 2, 7 | 14 | | | |
| Static Burn-In 2 Note 1 | 3 - 6, 8 - 13 | 7 | 1, 2, 14 | | | |
| Dynamic Burn- In Note 1 | 8, 10, 13 | 2, 7 | 14 | 3 - 6, 9, 11, 12 | 1 | |
| Irradiation Note 2 | 3 - 6, 8 - 13 | 7 | 1, 2, 14 | | | |
| PART NUMBER | CD4040BMS | | | | | 1 |
| Static Burn-In 1 Note 1 | 1 - 7, 9, 12 - 15 | 8, 10, 11 | 16 | | | |
| Static Burn-In 2 Note 1 | 1 - 7, 9, 12 - 15 | 8 | 10, 11, 16 | | | |
| Dynamic Burn- In Note 1 | - | 8, 11 | 16 | 1 - 7, 9, 12 - 15 | 10 | |
| Irradiation Note 2 | 1 - 7, 9, 12 - 15 | 8 | 10, 11, 16 | | | |

NOTE:

- 1. Each pin except VDD and GND will have a series resistor of 10K \pm 5%, VDD = 18V \pm 0.5V
- 2. Each pin except VDD and GND will have a series resistor of 47K ± 5%; Group E, Subgroup 2, sample size is 4 dice/wafer, 0 failures, VDD = 10V ± 0.5V

Functional Diagrams



Logic Diagrams

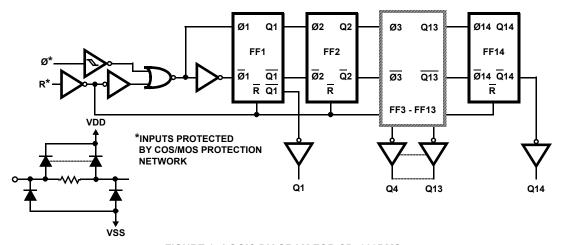


FIGURE 1. LOGIC DIAGRAM FOR CD4020BMS

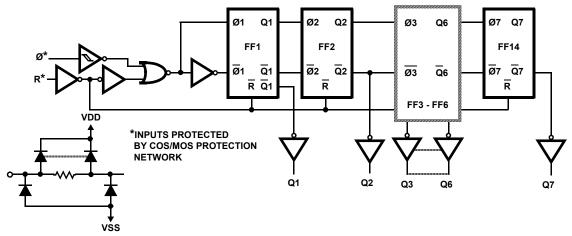


FIGURE 2. LOGIC DIAGRAM FOR CD4024BMS

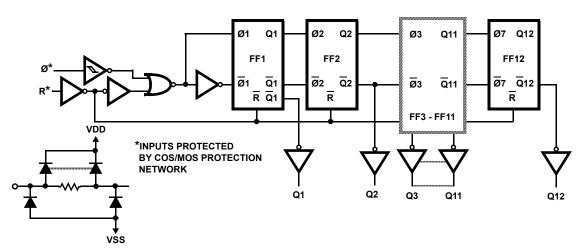


FIGURE 3. LOGIC DIAGRAM FOR CD4040BMS



Typical Performance Characteristics

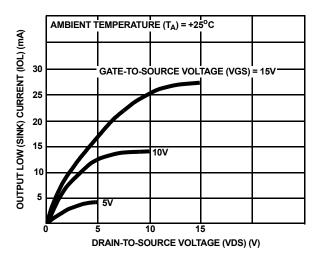


FIGURE 4. TYPICAL OUTPUT LOW (SINK) CURRENT CHARACTERISTICS

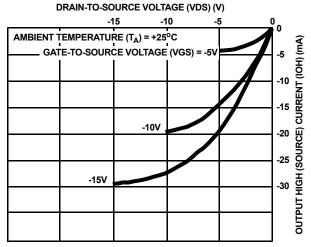


FIGURE 6. TYPICAL OUTPUT HIGH (SOURCE) CURRENT CHARACTERISTICS

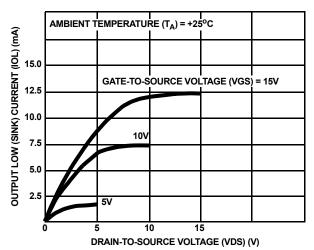


FIGURE 5. MINIMUM OUTPUT LOW (SINK) CURRENT CHARACTERISTICS

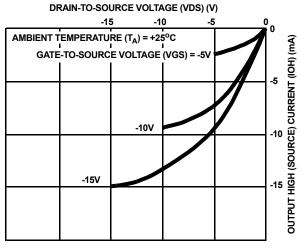


FIGURE 7. MINIMUM OUTPUT HIGH (SOURCE) CURRENT CHARACTERISTICS

Typical Performance Characteristics (Continued)

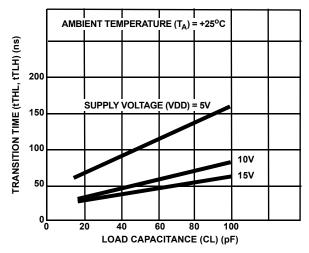


FIGURE 8. TYPICAL TRANSITION TIME AS A FUNCTION OF LOAD CAPACITANCE

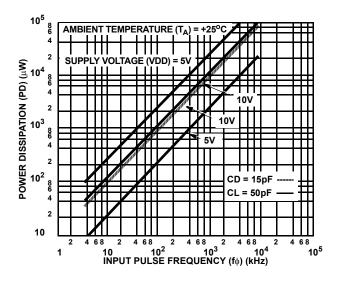
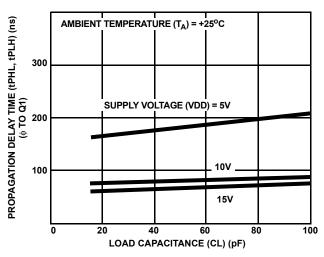
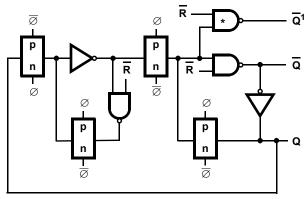


FIGURE 10. TYPICAL DYNAMIC POWER DISSIPATION AS A FUNCTION OF INPUT PULSE FREQUENCY FOR CD4020BMS

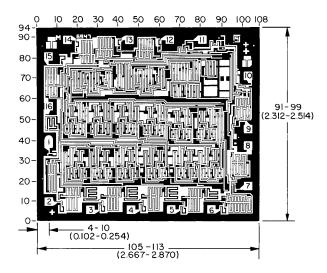


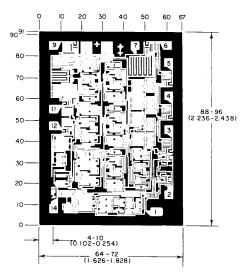


* ON FIRST STAGE ONLY

FIGURE 11. DETAIL OF TYPICAL FLIP-FLOP STAGES

Chip Dimensions and Pad Layouts





Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10⁻³ inch)

DIMENSIONS AND PAD LAYOUT FOR CD4020BMS. DIMENSIONS AND PAD LAYOUT FOR CD4040BMS ARE IDENTICAL

DIMENSIONS AND PAD LAYOUT FOR CD4024BMSH

METALLIZATION: Thickness: 11kÅ - 14kÅ, AL.

PASSIVATION: 10.4kÅ - 15.6kÅ, Silane

BOND PADS: 0.004 inches X 0.004 inches MIN **DIE THICKNESS:** 0.0198 inches - 0.0218 inches

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